

# **PSMN4R3-100PS**

# N-channel 100 V 4.3 m $\Omega$ standard level MOSFET in TO-220

Rev. 1 — 27 October 2011

Product data sheet

## 1. Product profile

### 1.1 General description

Standard level N-channel MOSFET in a TO-220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

### 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

| Symbol   | Parameter   | Conditions   |     | Min | Тур | Max | Unit |
|--|---|--|-----|-----|-----|-----|------|
| $V_{DS}$   | drain-source voltage  | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C  |     | -   | -   | 100 | V    |
| I <sub>D</sub>                                     | drain current   | $T_{mb}$ = 25 °C; $V_{GS}$ = 10 V;<br>see Figure 1   | [1] | -   | -   | 120 | Α    |
| P <sub>tot</sub>                                   | total power dissipation   | T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>   |     | -   | -   | 338 | W    |
| T <sub>j</sub>                                     | junction temperature  |  |     | -55 | -   | 175 | °C   |
| Static charac                                      | teristics   |  |     |     |     |     |      |
| R <sub>DSon</sub> drain-source on-state resistance | $V_{GS} = 10 \text{ V; } I_D = 25 \text{ A; } T_j = 100 \text{ °C;}$<br>see Figure 12 |  | -   | 6.6 | 7.8 | mΩ  |      |
|  |   | $V_{GS} = 10 \text{ V; } I_D = 25 \text{ A; } T_j = 25 \text{ °C;}$<br>see Figure 13                                 | [2] | -   | 3.7 | 4.3 | mΩ   |
| Dynamic cha  | racteristics  |  |     |     |     |     |      |
| $Q_{GD}$   | gate-drain charge   | $V_{GS} = 10 \text{ V}; I_D = 75 \text{ A}; V_{DS} = 50 \text{ V};$  |     | -   | 49  | -   | nC   |
| Q <sub>G(tot)</sub>                                | total gate charge   | see Figure 14; see Figure 15   |     | -   | 170 | -   | nC   |
| Avalanche ru                                       | ıggedness   |  |     |     |     |     |      |
| E <sub>DS(AL)S</sub>                               | non-repetitive drain-source avalanche energy  | $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C;<br>$I_D$ = 120 A; $V_{sup} \le$ 100 V;<br>$R_{GS}$ = 50 $\Omega$ ; Unclamped |     | -   | -   | 537 | mJ   |

<sup>[1]</sup> Continuous current limited by package



[2] Measured 3 mm from package.

# 2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description                       | Simplified outline | Graphic symbol        |
|-----|--------|-----------------------------------|--------------------|-----------------------|
| 1   | G      | gate                              |                    | _                     |
| 2   | D      | drain                             | mb                 | D                     |
| 3   | S      | source                            |                    | $G \longrightarrow A$ |
| mb  | D      | mounting base; connected to drain | 1 2 3              | mbb076 S              |
|     |        |                                   | SOT78 (TO-220AB)   |                       |

# 3. Ordering information

Table 3. Ordering information

| Type number   | Package  |  |         |
|---------------|----------|--|---------|
|               | Name     | Description  | Version |
| PSMN4R3-100PS | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78   |

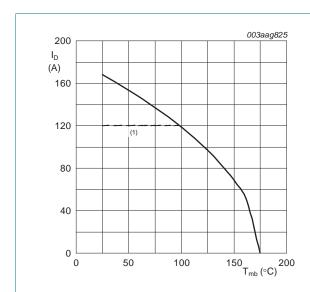
# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol               | Parameter                                    | Conditions   |            | Min | Max | Unit |
|----------------------|--|--|------------|-----|-----|------|
| V <sub>DS</sub>      | drain-source voltage                         | T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C  |            | -   | 100 | ٧    |
| $V_{DGR}$            | drain-gate voltage                           | $T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ  |            | -   | 100 | V    |
| $V_{GS}$             | gate-source voltage                          |  |            | -20 | 20  | V    |
| I <sub>D</sub>       | drain current                                | $V_{GS} = 10 \text{ V}; T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{}$                         |            | -   | 119 | Α    |
|                      |  | $V_{GS} = 10 \text{ V; } T_{mb} = 25 \text{ °C; see } \frac{\text{Figure 1}}{}$                              | <u>[1]</u> | -   | 120 | Α    |
| I <sub>DM</sub>      | peak drain current                           | pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 \text{ °C}$ ; see Figure 3   |            | -   | 673 | Α    |
| P <sub>tot</sub>     | total power dissipation                      | T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>   |            | -   | 338 | W    |
| T <sub>stg</sub>     | storage temperature                          |  |            | -55 | 175 | °C   |
| Tj                   | junction temperature                         |  |            | -55 | 175 | °C   |
| $T_{sld(M)}$         | peak soldering temperature                   |  |            | -   | 260 | °C   |
| Source-drai          | in diode                                     |  |            |     |     |      |
| Is                   | source current                               | T <sub>mb</sub> = 25 °C  | <u>[1]</u> | -   | 120 | Α    |
| I <sub>SM</sub>      | peak source current                          | pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$   |            | -   | 673 | Α    |
| Avalanche i          | ruggedness                                   |  |            |     |     |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-source avalanche energy | $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 120 A; $V_{sup}$ ≤ 100 V; $R_{GS}$ = 50 $\Omega$ ; Unclamped |            | -   | 537 | mJ   |
|                      |  |  |            |     |     |      |

### [1] Continuous current limited by package



 $V_{GS} \ge 10 V$ ; (1) Capped at 120A due to package

Fig 1. Continuous drain current as a function of mounting base temperature

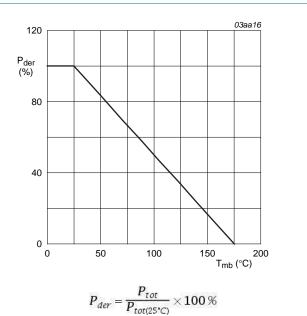
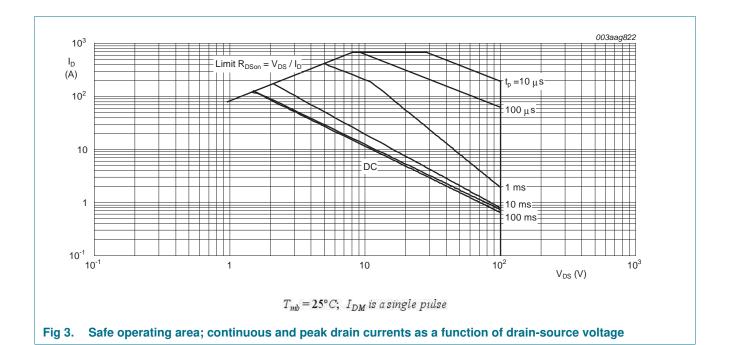


Fig 2. Normalized total power dissipation as a function of mounting base temperature

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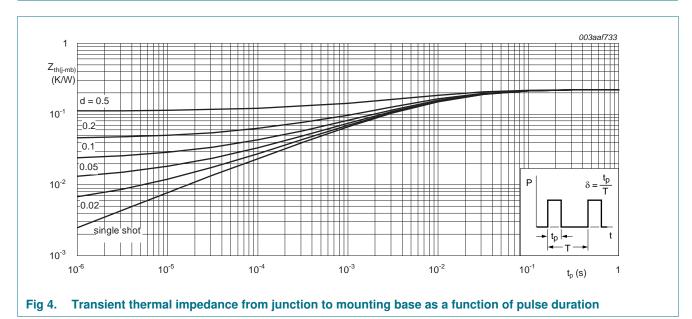
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## 5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol               | Parameter   | Conditions           | Min | Тур  | Max  | Unit |
|----------------------|---|----------------------|-----|------|------|------|
| $R_{th(j-mb)}$       | thermal resistance from junction to mounting base | see Figure 4         | -   | 0.22 | 0.44 | K/W  |
| R <sub>th(j-a)</sub> | thermal resistance from junction to ambient       | vertical in free air | -   | 60   | -    | K/W  |



# 6. Characteristics

Table 6 Characteristics

| Table 6.   | Characteristics   |   |     |      |     |      |
|--|---|---|-----|------|-----|------|
| Symbol   | Parameter   | Conditions  | Min | Тур  | Max | Unit |
| Static cha   | aracteristics   |   |     |      |     |      |
| $V_{(BR)DSS}$                                      | drain-source breakdown  | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$  | 100 | -    | -   | V    |
|  | voltage   | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$   | 90  | -    | -   | V    |
| $V_{GS(th)}$                                       | gate-source threshold voltage   | $I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = -55 \text{ °C}$ ; see Figure 10                       | -   | -    | 4.6 | V    |
|  |   | $I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 175$ °C; see Figure 10   | 1   | -    | -   | V    |
|  |   | $I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see Figure 11; see Figure 10                           | 2   | 3    | 4   | V    |
| I <sub>DSS</sub>                                   | drain leakage current   | $V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$                                     | -   | 0.08 | 10  | μΑ   |
|  |   | $V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$                                    | -   | -    | 500 | μΑ   |
| $I_{GSS}$  | gate leakage current  | $V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C   | -   | 10   | 100 | nΑ   |
|  |   | $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$                                      | -   | 10   | 100 | nΑ   |
| R <sub>DSon</sub> drain-source on-state resistance |   | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C};$ see Figure 12                        | -   | 10.4 | 12  | mΩ   |
|  |   | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$<br>see Figure 12                     | -   | 6.6  | 7.8 | mΩ   |
|  | $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$<br>see <u>Figure 13</u> | [1] -   | 3.7 | 4.3  | mΩ  |      |
| R <sub>G</sub>                                     | gate resistance   | f = 1 MHz   | -   | 0.9  | -   | Ω    |
| Dynamic  | characteristics   |   |     |      |     |      |
| Q <sub>G(tot)</sub>                                | total gate charge   | $I_D = 75 \text{ A}$ ; $V_{DS} = 50 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see Figure 14; see Figure 15 | -   | 170  | -   | nC   |
|  |   | $I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$  | -   | 140  | -   | nC   |
| Q <sub>GS</sub>                                    | gate-source charge  | $I_D = 75 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V}; \text{see}$                          | -   | 48   | -   | nC   |
| Q <sub>GS(th)</sub>                                | pre-threshold gate-source charge  | Figure 14; see Figure 15  | -   | 31   | -   | nC   |
| Q <sub>GS(th-pl)</sub>                             | post-threshold gate-source charge   |   | -   | 17.3 | -   | nC   |
| Q <sub>GD</sub>                                    | gate-drain charge   |   | -   | 49   | -   | nC   |
| $V_{GS(pl)}$                                       | gate-source plateau voltage   | V <sub>DS</sub> = 50 V; see <u>Figure 14</u> ; see <u>Figure 15</u>                                     | -   | 5.1  | -   | V    |
| C <sub>iss</sub>                                   | input capacitance   | $V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$                                       | -   | 9900 | -   | pF   |
| C <sub>oss</sub>                                   | output capacitance  | T <sub>j</sub> = 25 °C; see <u>Figure 16</u>  | -   | 660  | -   | pF   |
| C <sub>rss</sub>                                   | reverse transfer capacitance  |   | -   | 381  | -   | pF   |
| t <sub>d(on)</sub>                                 | turn-on delay time  | $V_{DS} = 50 \text{ V}; R_L = 0.67 \Omega; V_{GS} = 10 \text{ V};$                                      | -   | 45   | -   | ns   |
| t <sub>r</sub>                                     | rise time   | $R_{G(ext)} = 4.7 \Omega$ ; $I_D = 75 A$ ; $T_j = 25 °C$  | -   | 91   | -   | ns   |
| t <sub>d(off)</sub>                                | turn-off delay time   |   | -   | 122  | -   | ns   |
| t <sub>f</sub>                                     | fall time   |   | -   | 63   | -   | ns   |

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4.5

0.8 V<sub>DS</sub> (V)

### N-channel 100 V 4.3 mΩ standard level MOSFET in TO-220

Table 6. Characteristics ... continued

| Symbol          | Parameter             | Conditions  | Min | Тур | Max | Unit |
|-----------------|-----------------------|---|-----|-----|-----|------|
| Source-drain    | n diode               |   |     |     |     |      |
| $V_{SD}$        | source-drain voltage  | $I_S$ = 25 A; $V_{GS}$ = 0 V; $T_j$ = 25 °C; see <u>Figure 17</u> | -   | 0.8 | 1.2 | V    |
| t <sub>rr</sub> | reverse recovery time | $I_S = 25 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ;   | -   | 75  | -   | ns   |
| Q <sub>r</sub>  | recovered charge      | $V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$                     | -   | 235 | -   | nC   |

### [1] Measured 3 mm from package.

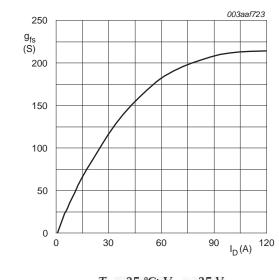
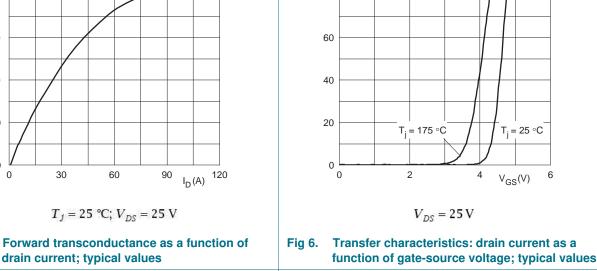
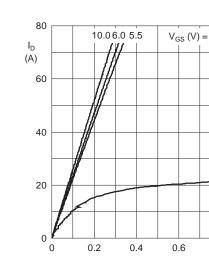


Fig 5. Forward transconductance as a function of



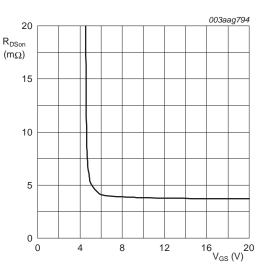
100

 $I_D$ 





 $T_i = 25^{\circ}C$ 



Drain-source on-state resistance as a function of gate-source voltage; typical values

 $T_j = 25^{\circ}C; I_D = 25A$ 

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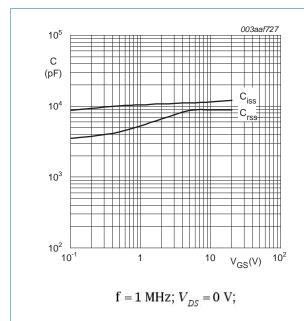


Fig 9. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

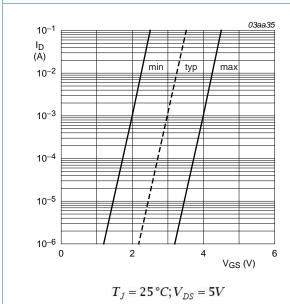


Fig 11. Sub-threshold drain current as a function of gate-source voltage

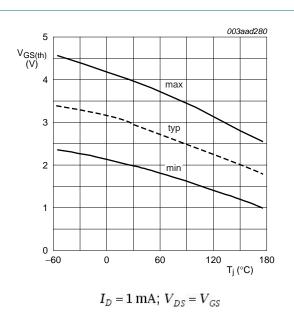


Fig 10. Gate-source threshold voltage as a function of junction temperature

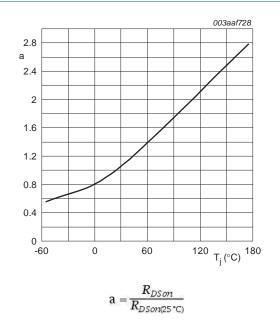
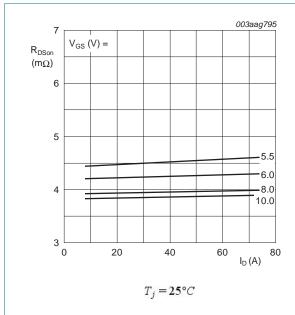


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



V<sub>GS</sub>(pl)

V<sub>GS</sub>(th)

V<sub>GS</sub>

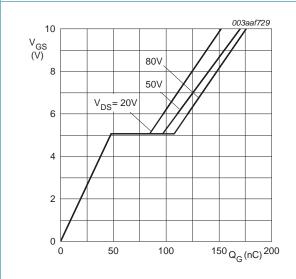
Q<sub>GS1</sub> Q<sub>GS2</sub>

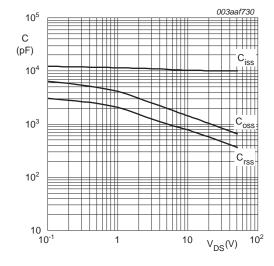
Q<sub>GS</sub> Q<sub>G</sub>(tot)

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Fig 13. Drain-source on-state resistance as a function of drain current; typical values

Fig 14. Gate charge waveform definitions





 $T_j = 25$  °C;  $I_D = 75$  A

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical

 $V_{GS} = 0 \text{ V}; f = 1 \text{MHz}$ 

Fig 15. Gate-source voltage as a function of gate charge; typical values

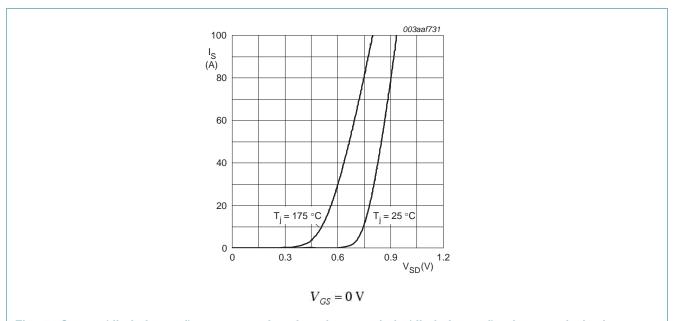
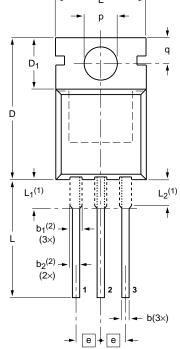


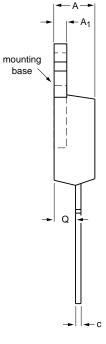
Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

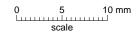
# 7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78







### DIMENSIONS (mm are the original dimensions)

| UNI | ГА         | A <sub>1</sub> | b          | b <sub>1</sub> (2) | b <sub>2</sub> (2) | С          | D            | D <sub>1</sub> | E           | е    | L            | L <sub>1</sub> (1) | L <sub>2</sub> <sup>(1)</sup><br>max. | р          | q          | Q          |
|-----|------------|----------------|------------|--------------------|--------------------|------------|--------------|----------------|-------------|------|--------------|--------------------|---------------------------------------|------------|------------|------------|
| mm  | 4.7<br>4.1 | 1.40<br>1.25   | 0.9<br>0.6 | 1.6<br>1.0         | 1.3<br>1.0         | 0.7<br>0.4 | 16.0<br>15.2 | 6.6<br>5.9     | 10.3<br>9.7 | 2.54 | 15.0<br>12.8 | 3.30<br>2.79       | 3.0                                   | 3.8<br>3.5 | 3.0<br>2.7 | 2.6<br>2.2 |

#### Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

| OUTLINE |     | REFER           | ENCES |  | ISSUE DATE |                                 |  |
|---------|-----|-----------------|-------|--|------------|---------------------------------|--|
| VERSION | IEC | JEDEC           | JEITA |  | PROJECTION | ISSUE DATE                      |  |
| SOT78   |     | 3-lead TO-220AB | SC-46 |  |            | <del>08-04-23</del><br>08-06-13 |  |

Fig 18. Package outline SOT78 (TO-220AB)

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# 8. Revision history

### Table 7. Revision history

| Document ID       | Release date | Data sheet status  | Change notice | Supersedes |
|-------------------|--------------|--------------------|---------------|------------|
| PSMN4R3-100PS v.1 | 20111027     | Product data sheet | -             | -          |

## 9. Legal information

#### 9.1 Data sheet status

| Document status [1] [2]        | Product status [3] | Definition  |
|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification      | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production         | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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#### N-channel 100 V 4.3 mΩ standard level MOSFET in TO-220

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# **PSMN4R3-100PS**

## **Nexperia**

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